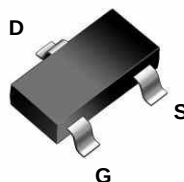
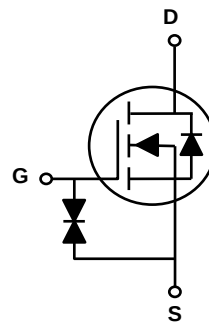


### Main Product Characteristics

|               |               |
|---------------|---------------|
| $V_{(BR)DSS}$ | 20V           |
| $R_{DS(ON)}$  | 300m $\Omega$ |
| $I_D$         | 800mA         |



SOT-523



Schematic Diagram

### Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



### Description

The SSF2320Y utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

### Absolute Maximum Ratings ( $T_C=25^{\circ}\text{C}$ unless otherwise specified)

| Parameter                                                | Symbol    | Rating      | Unit                   |
|----------------------------------------------------------|-----------|-------------|------------------------|
| Drain-Source Voltage                                     | $V_{DS}$  | 20          | V                      |
| Gate-Source Voltage                                      | $V_{GS}$  | $\pm 8$     | V                      |
| Drain Current – Continuous ( $T_C=25^{\circ}\text{C}$ )  | $I_D$     | 800         | mA                     |
| Drain Current – Continuous ( $T_C=100^{\circ}\text{C}$ ) |           | 510         | mA                     |
| Drain Current – Pulsed <sup>1</sup>                      | $I_{DM}$  | 3.2         | A                      |
| Power Dissipation ( $T_C=25^{\circ}\text{C}$ )           | $P_D$     | 312         | mW                     |
| Power Dissipation – Derate above $25^{\circ}\text{C}$    |           | 2.5         | mW/ $^{\circ}\text{C}$ |
| Storage Temperature Range                                | $T_{STG}$ | -55 to +150 | $^{\circ}\text{C}$     |
| Operating Junction Temperature Range                     | $T_J$     | -55 to +150 | $^{\circ}\text{C}$     |

### Thermal Characteristics

| Parameter                              | Symbol          | Typ. | Max. | Unit                 |
|----------------------------------------|-----------------|------|------|----------------------|
| Thermal Resistance Junction to Ambient | $R_{\theta JA}$ | ---  | 400  | $^{\circ}\text{C/W}$ |

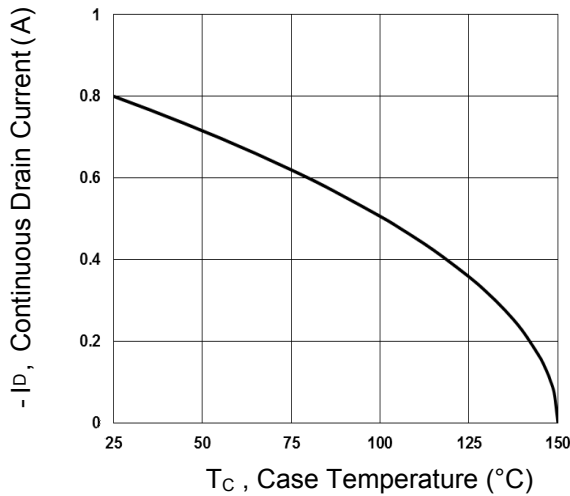
**Electrical Characteristics** ( $T_J=25^{\circ}\text{C}$  unless otherwise specified)

| Parameter                                              | Symbol                              | Conditions                                                                                  | Min. | Typ.  | Max. | Unit  |
|--------------------------------------------------------|-------------------------------------|---------------------------------------------------------------------------------------------|------|-------|------|-------|
| Off Characteristics                                    |                                     |                                                                                             |      |       |      |       |
| Drain-Source Breakdown Voltage                         | BV <sub>DSS</sub>                   | V <sub>GS</sub> =0V , I <sub>D</sub> =250uA                                                 | 20   | ---   | ---  | V     |
| BV <sub>DSS</sub> Temperature Coefficient              | ΔBV <sub>DSS</sub> /ΔT <sub>J</sub> | Reference to 25°C , I <sub>D</sub> =1mA                                                     | ---  | -0.01 | ---  | V/°C  |
| Drain-Source Leakage Current                           | I <sub>DSS</sub>                    | V <sub>DS</sub> =20V , V <sub>GS</sub> =0V, T <sub>J</sub> =25°C                            | ---  | ---   | 1    | uA    |
|                                                        |                                     | V <sub>DS</sub> =16V , V <sub>GS</sub> =0V,T <sub>J</sub> =125°C                            | ---  | ---   | 10   | uA    |
| Gate-Source Leakage Current                            | I <sub>GSS</sub>                    | V <sub>GS</sub> =±6V , V <sub>DS</sub> =0V                                                  | ---  | ---   | ±20  | uA    |
| On Characteristics                                     |                                     |                                                                                             |      |       |      |       |
| Static Drain-Source On-Resistance                      | R <sub>DS(ON)</sub>                 | V <sub>GS</sub> =4.5V , I <sub>D</sub> =0.5A                                                | ---  | 200   | 300  | mΩ    |
|                                                        |                                     | V <sub>GS</sub> =2.5V , I <sub>D</sub> =0.4A                                                | ---  | 235   | 400  |       |
|                                                        |                                     | V <sub>GS</sub> =1.8V , I <sub>D</sub> =0.2A                                                | ---  | 295   | 550  |       |
|                                                        |                                     | V <sub>GS</sub> =1.5V , I <sub>D</sub> =0.1A                                                | ---  | 365   | 800  |       |
|                                                        |                                     | V <sub>GS</sub> =1.2V , I <sub>D</sub> =0.1A                                                | ---  | 600   | 1500 |       |
| Gate Threshold Voltage                                 | V <sub>GS(th)</sub>                 | V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA                                    | 0.3  | 0.6   | 1.0  | V     |
| V <sub>GS(th)</sub> Temperature Coefficient            | ΔV <sub>GS(th)</sub>                |                                                                                             | ---  | 3     | ---  | mV/°C |
| Dynamic and Switching Characteristics                  |                                     |                                                                                             |      |       |      |       |
| Total Gate Charge <sup>2, 3</sup>                      | Q <sub>g</sub>                      | V <sub>DS</sub> =10V , V <sub>GS</sub> =4.5V , I <sub>D</sub> =0.5A                         | ---  | 1     | 2    | nC    |
| Gate-Source Charge <sup>2, 3</sup>                     | Q <sub>gs</sub>                     |                                                                                             | ---  | 0.26  | 0.5  |       |
| Gate-Drain Charge <sup>2, 3</sup>                      | Q <sub>gd</sub>                     |                                                                                             | ---  | 0.2   | 0.4  |       |
| Turn-On Delay Time <sup>2, 3</sup>                     | T <sub>d(on)</sub>                  | V <sub>DD</sub> =10V , V <sub>GS</sub> =4.5V ,<br>R <sub>G</sub> =10Ω, I <sub>D</sub> =0.5A | ---  | 5     | 10   | nS    |
| Rise Time <sup>2, 3</sup>                              | T <sub>r</sub>                      |                                                                                             | ---  | 3.5   | 7    |       |
| Turn-Off Delay Time <sup>2, 3</sup>                    | T <sub>d(off)</sub>                 |                                                                                             | ---  | 14    | 28   |       |
| Fall Time <sup>2, 3</sup>                              | T <sub>f</sub>                      |                                                                                             | ---  | 6     | 12   |       |
| Input Capacitance                                      | C <sub>iss</sub>                    | V <sub>DS</sub> =10V , V <sub>GS</sub> =0V , F=1MHz                                         | ---  | 38.2  | 75   | pF    |
| Output Capacitance                                     | C <sub>oss</sub>                    |                                                                                             | ---  | 14.4  | 28   |       |
| Reverse Transfer Capacitance                           | C <sub>rss</sub>                    |                                                                                             | ---  | 6     | 12   |       |
| Drain-Source Diode Characteristics and Maximum Ratings |                                     |                                                                                             |      |       |      |       |
| Parameter                                              | Symbol                              | Conditions                                                                                  | Min. | Typ.  | Max. | Unit  |
| Continuous Source Current                              | I <sub>S</sub>                      | V <sub>G</sub> =V <sub>D</sub> =0V , Force Current                                          | ---  | ---   | 0.8  | A     |
| Pulsed Source Current                                  | I <sub>SM</sub>                     |                                                                                             | ---  | ---   | 1.6  | A     |
| Diode Forward Voltage                                  | V <sub>SD</sub>                     | V <sub>GS</sub> =0V , I <sub>S</sub> =0.2A , T <sub>J</sub> =25°C                           | ---  | ---   | 1    | V     |

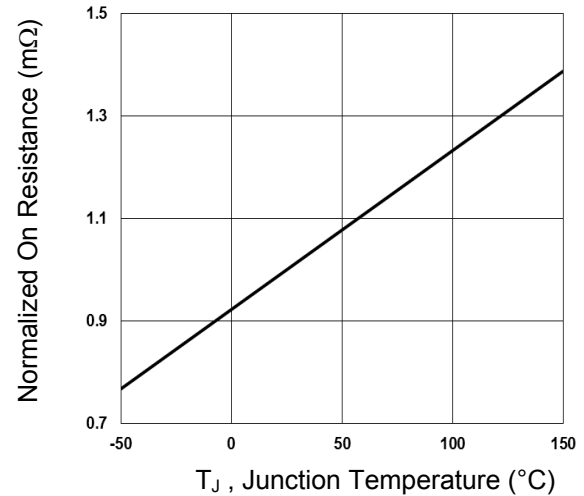
Note:

1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
3. Essentially independent of operating temperature.

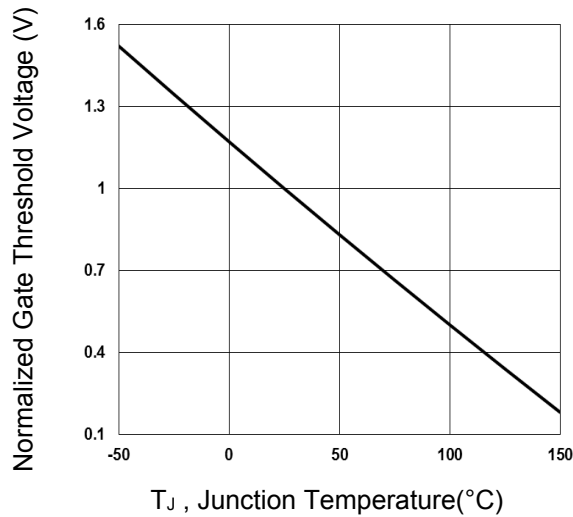
## Typical Electrical and Thermal Characteristic Curves



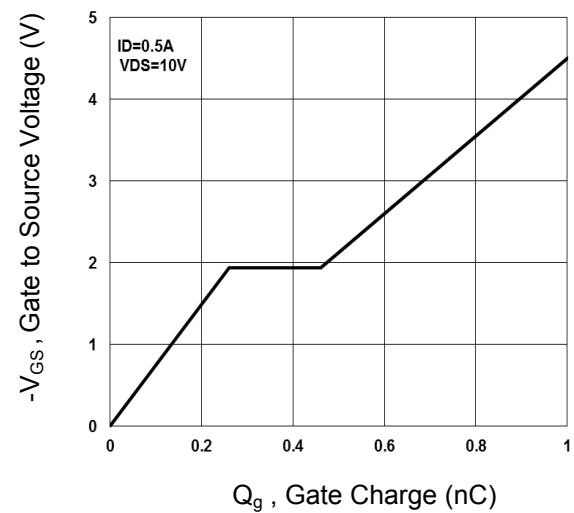
**Fig.1 Continuous Drain Current vs.  $T_C$**



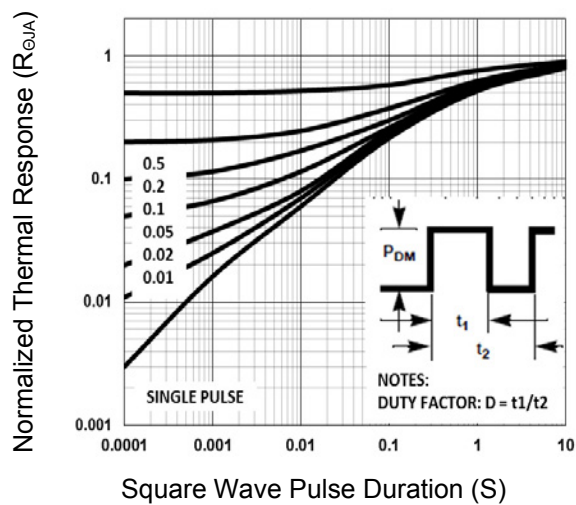
**Fig.2 Normalized  $R_{DS(ON)}$  vs.  $T_J$**



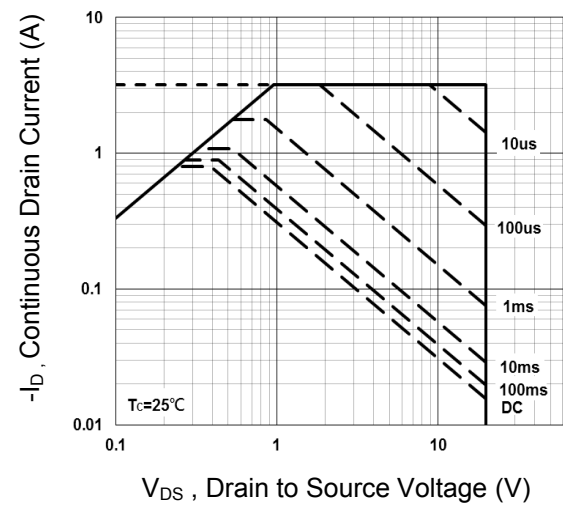
**Fig.3 Normalized  $V_{th}$  vs  $T_J$**



**Fig.4 Gate Charge Waveform**

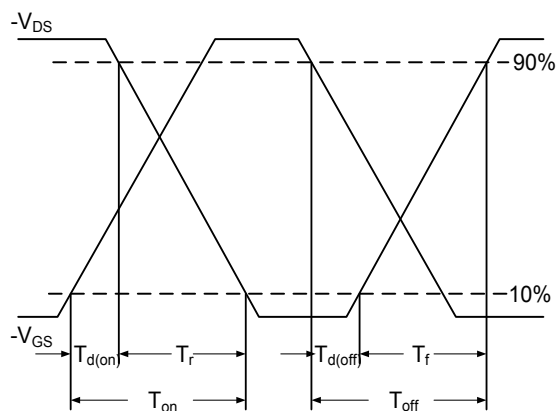


**Fig.5 Normalized Transient Impedance**

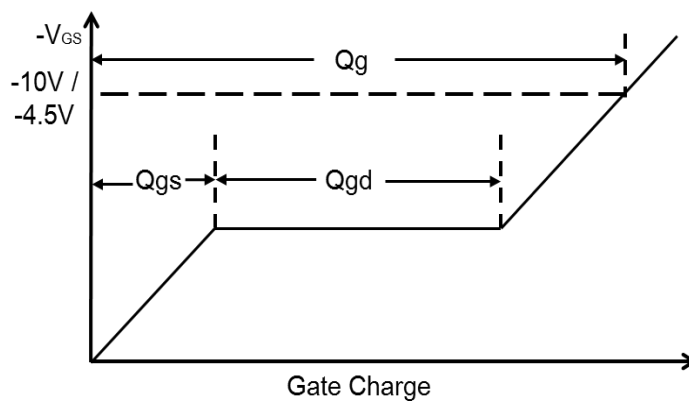


**Fig.6 Maximum Safe Operation Area**

## Typical Electrical and Thermal Characteristic Curves



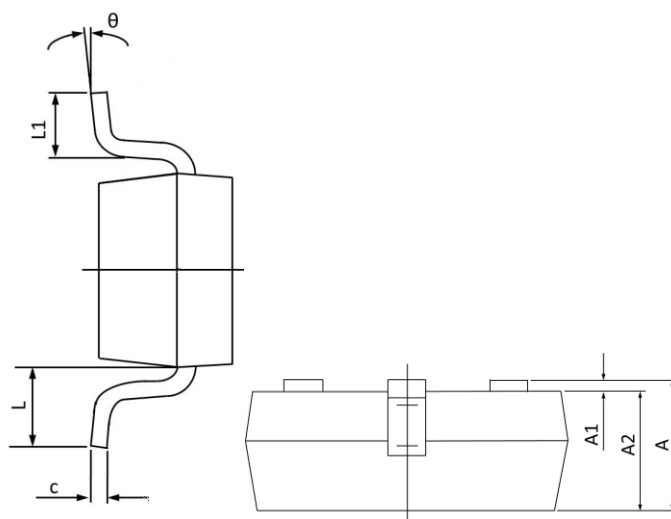
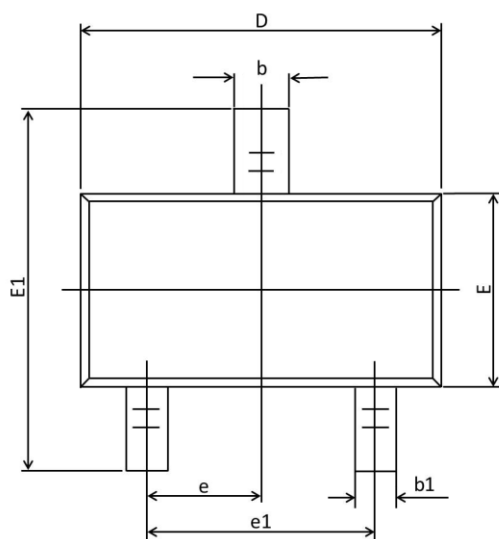
**Fig.7** Switching Time Waveform



**Fig.8** Gate Charge Waveform

## Package Outline Dimensions

## SOT-523



| Symbol | Dimensions In Millimeters |       | Dimensions In Inches |       |
|--------|---------------------------|-------|----------------------|-------|
|        | MAX                       | MIN   | MAX                  | MIN   |
| A      | 0.900                     | 0.700 | 0.035                | 0.028 |
| A1     | 0.100                     | 0.000 | 0.004                | 0.000 |
| A2     | 0.800                     | 0.700 | 0.031                | 0.028 |
| b      | 0.350                     | 0.250 | 0.014                | 0.010 |
| b1     | 0.250                     | 0.150 | 0.010                | 0.006 |
| c      | 0.200                     | 0.100 | 0.008                | 0.004 |
| D      | 1.750                     | 1.500 | 0.069                | 0.059 |
| E      | 0.900                     | 0.700 | 0.035                | 0.028 |
| E1     | 1.750                     | 1.400 | 0.069                | 0.055 |
| e      | 0.5TYP.                   |       | 0.02TYP.             |       |
| e1     | 1.100                     | 0.900 | 0.043                | 0.035 |
| L      | 0.460                     | 0.300 | 0.018                | 0.012 |
| L1     | 0.460                     | 0.260 | 0.018                | 0.010 |
| θ      | 8°                        | 0°    | 8°                   | 0°    |

## Order Information

| Device   | Package | Marking Code | Carrier     | Quantity  | HSF Status     |
|----------|---------|--------------|-------------|-----------|----------------|
| SSF2320Y | SOT-523 | B            | Tape & Reel | 3000/Reel | RoHS Compliant |